IN THE SPECIFICATION

Please add the following paragraph immediately after the title to the present application on page 1:

CROSS-REFERENCE TO RELATED APPLICATIONS

The present application is a continuation of U.S. Patent Application No. 09/840,748 filed 23 April 2001.

Please add the following paragraph immediately after the first full paragraph on page 3:

Another embodiment of the present invention includes a method of making a spinel-structured metal oxide on a substrate by molecular beam epitaxy. The metal oxide comprises oxygen atoms, first metal atoms, and at least one other metal atoms. The metal atoms substantially occupy thermodynamically stable lattice positions of the metal oxide. The method comprises the steps of: providing a substrate in a growth chamber; reducing the pressure in the growth chamber to a pressure suitable for epitaxial growth by molecular beam epitaxy; heating the substrate to a suitable growth temperature; supplying activated oxygen, a first metal atom flux, and at least one other metal atom flux to the surface of the substrate, wherein the metal atom fluxes are individually controlled at the substrate so as to grow the spinel-structured metal oxide having the metal atoms substantially occupying thermodynamically stable lattice positions of the metal oxide during the growth of the metal oxide; terminating the supply of the activated oxygen, the first metal atom flux, and the at least one other metal atom flux at the surface of the

substrate once the desired thickness of the metal oxide is formed on the substrate; and cooling the metal oxide to room temperature. This embodiment can further comprise the step of growing a spinel buffer layer on the substrate by molecular beam epitaxy prior to growing the metal oxide on the substrate.